

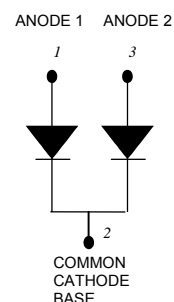
MUR3020WT ULTRAFAST PLASTIC RECTIFIER

Applications:

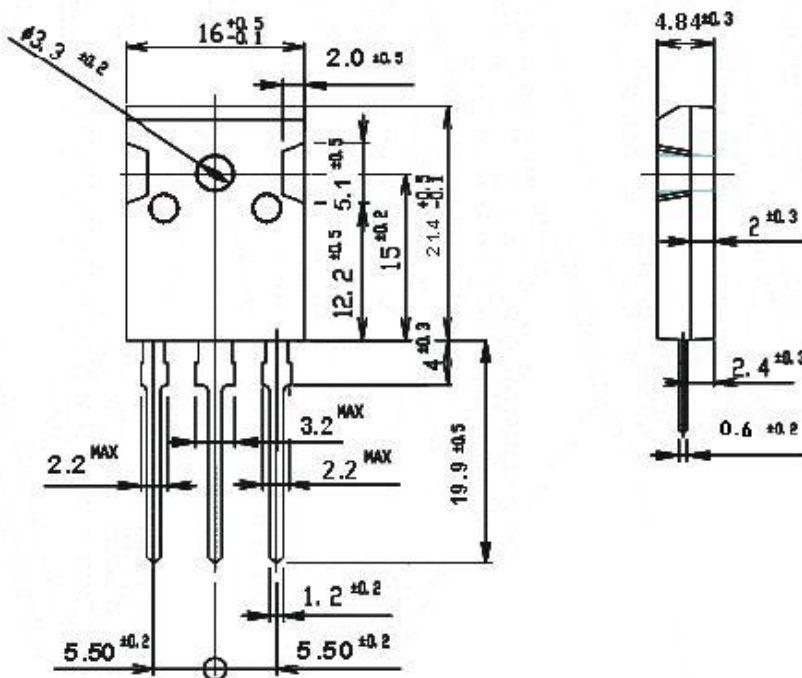
- Switching Power Supply
- Power Switching Circuits
- General Purpose

Features:

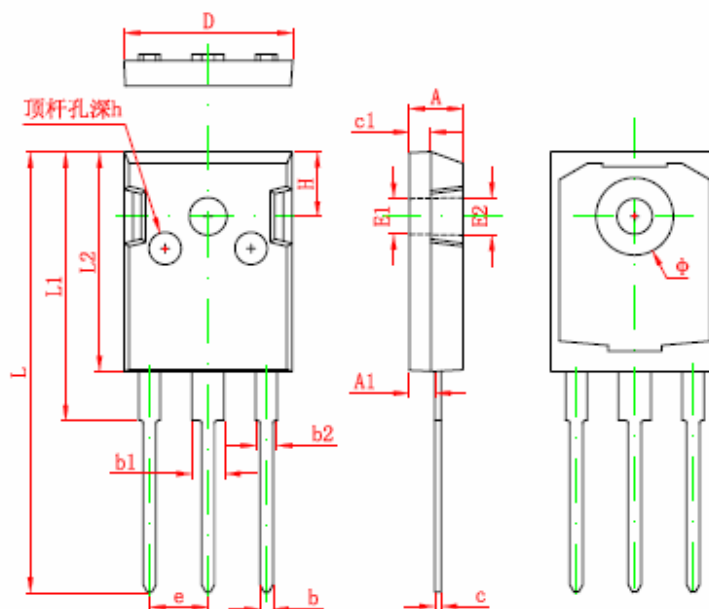
- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Dimensions: In mm/Inches



OPTION 1(SR)

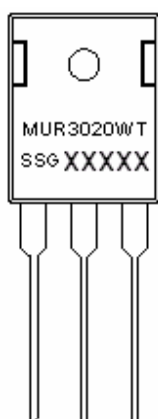


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	
h	0.000	0.300	0.000	0.012

OPTION 2(CJ)

TO-247AD

Marking Diagram:



Where XXXXX is YYWWL

MUR = Device Type
30 = Forward Current (30A)
20 = Reverse Voltage (200V)
WT = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MUR3020WT	TO-247AD (Pb-Free)	30 pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @Tc=125°C, rectangular wave form	30	A
Max. Peak One Cycle Non-Repetitive Surge Current (Per leg)	I_{FSM}	8.3ms, Half Sine pulse	110	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop* (Per leg)	V_{F1}	@15A, Pulse, $T_J = 25^\circ\text{C}$	1.05	V
Reverse Current* (Per leg)	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	10	μA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	3.5	mA
Reverse Recovery Time	t_{rr}	$I_F=500\text{mA}$, $I_R=1\text{A}$, and $I_{rm}=250\text{mA}$	35	ns

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	1.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	6.7	g
Case Style	TO-247AD			

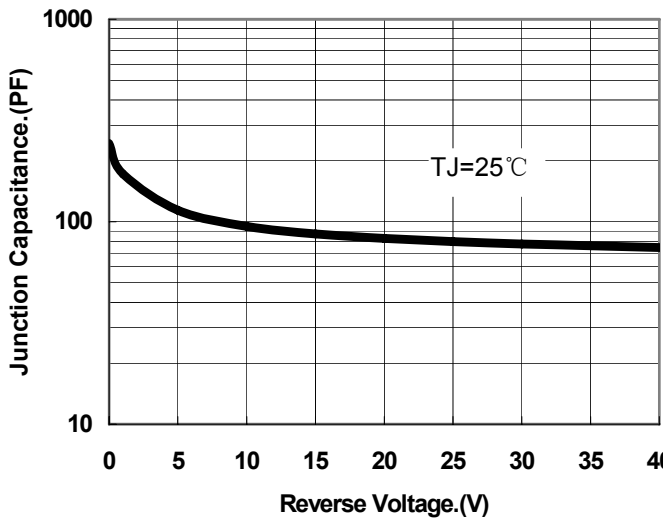


Fig.1-Typical Junction Capacitance

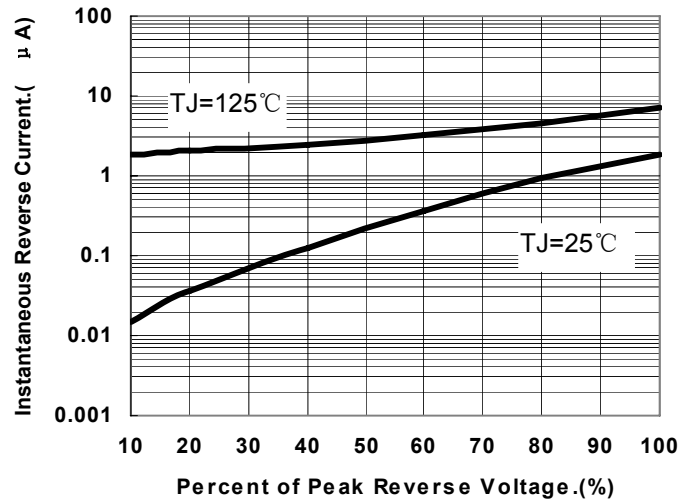


Fig.2-Typical Reverse Characteristics

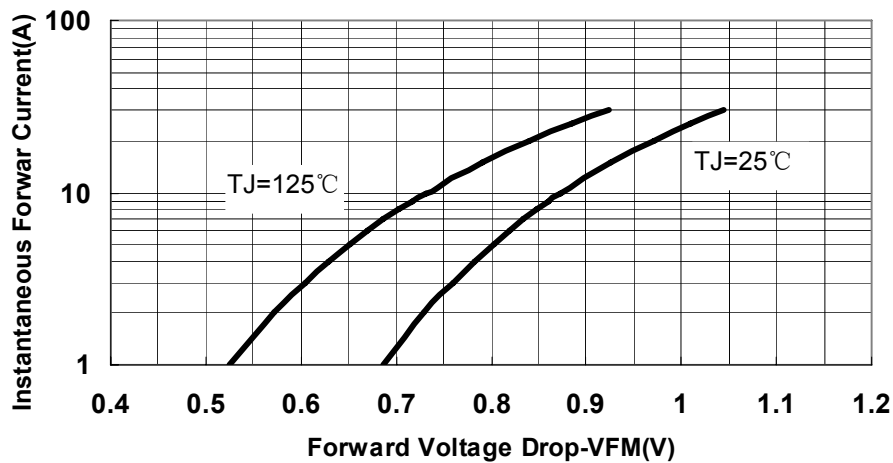


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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